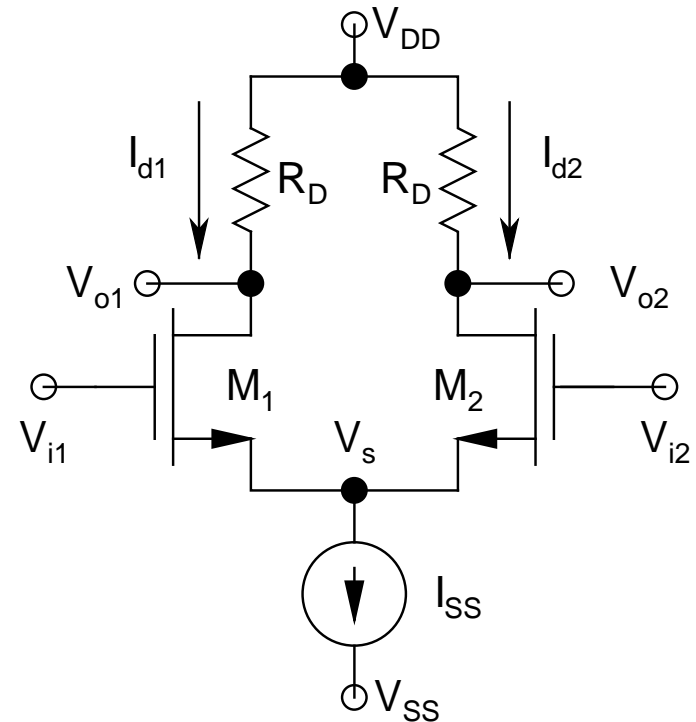


- **NMOS DA (SCP):**

- M_1 - M_2 constitute a *perfectly matched pair*, and have their *sources connected together*, hence, the name
- I_{SS} : **DC bias current source**
- *All voltages and currents are instantaneous*



NMOS DA Topology

➤ $V_{gs1} = V_{i1} - V_s$, and $V_{gs2} = V_{i2} - V_s$

➤ ***KVL around M_1 - M_2 GS loop:***

$$V_{i1} - V_{gs1} + V_{gs2} - V_{i2} = 0$$

$$\Rightarrow V_{gs1} - V_{gs2} = V_{i1} - V_{i2} = V_{id}$$

➤ ***Neglecting CLM Effect:***

$$I_{d1} = \frac{k'_N}{2} \left(\frac{W}{L} \right) (V_{gs1} - V_{TN1})^2 \quad \text{and}$$

$$I_{d2} = \frac{k'_N}{2} \left(\frac{W}{L} \right) (V_{gs2} - V_{TN2})^2$$

- Ran into a problem, since *both M_1 and M_2 would have body effect present*
 - *Both bodies connected to V_{SS} , but the common source node is at a floating potential V_s*
 \Rightarrow Analytical evaluation of I_{d1} and I_{d2} becomes pretty tedious
- *If the CLM effect is also included, then the problem would need numerical solution!*
- To get a *first-order estimate, neglect body effect*

$$\Rightarrow V_{TN1} = V_{TN2} = V_{TN0}$$

➤ Thus:

$$V_{id} = \frac{\sqrt{I_{d1}} - \sqrt{I_{d2}}}{\sqrt{\frac{k'_N}{2} \left(\frac{W}{L} \right)}} \quad (1)$$

➤ Also:

$$I_{d1} + I_{d2} = I_{SS} \quad (2)$$

➤ ***Solving Eqs.(1) and (2):***

$$I_{d1} = I_{SS}/2 + \xi \quad \text{and}$$

$$I_{d2} = I_{SS}/2 - \xi$$

$$\xi = \frac{k'_N}{4} \left(\frac{W}{L} \right) V_{id} \sqrt{\frac{4I_{SS}}{k'_N (W/L)} - V_{id}^2}$$

- For $V_{id} = 0$, $\xi = 0$, and $I_{d1} = I_{d2} = I_{SS}/2$
 - *Most preferred DC bias point of the circuit*
- For $V_{id} > 0$, $I_{d1} \uparrow$ and $I_{d2} \downarrow$
- For $V_{id} < 0$, $I_{d1} \downarrow$ and $I_{d2} \uparrow$
- But for both cases, the *sum of I_{d1} and I_{d2} remains constant at I_{SS}*
- *Linear Range* of this circuit is *defined by the values of V_{id} , which turns either M_1 or M_2 off*

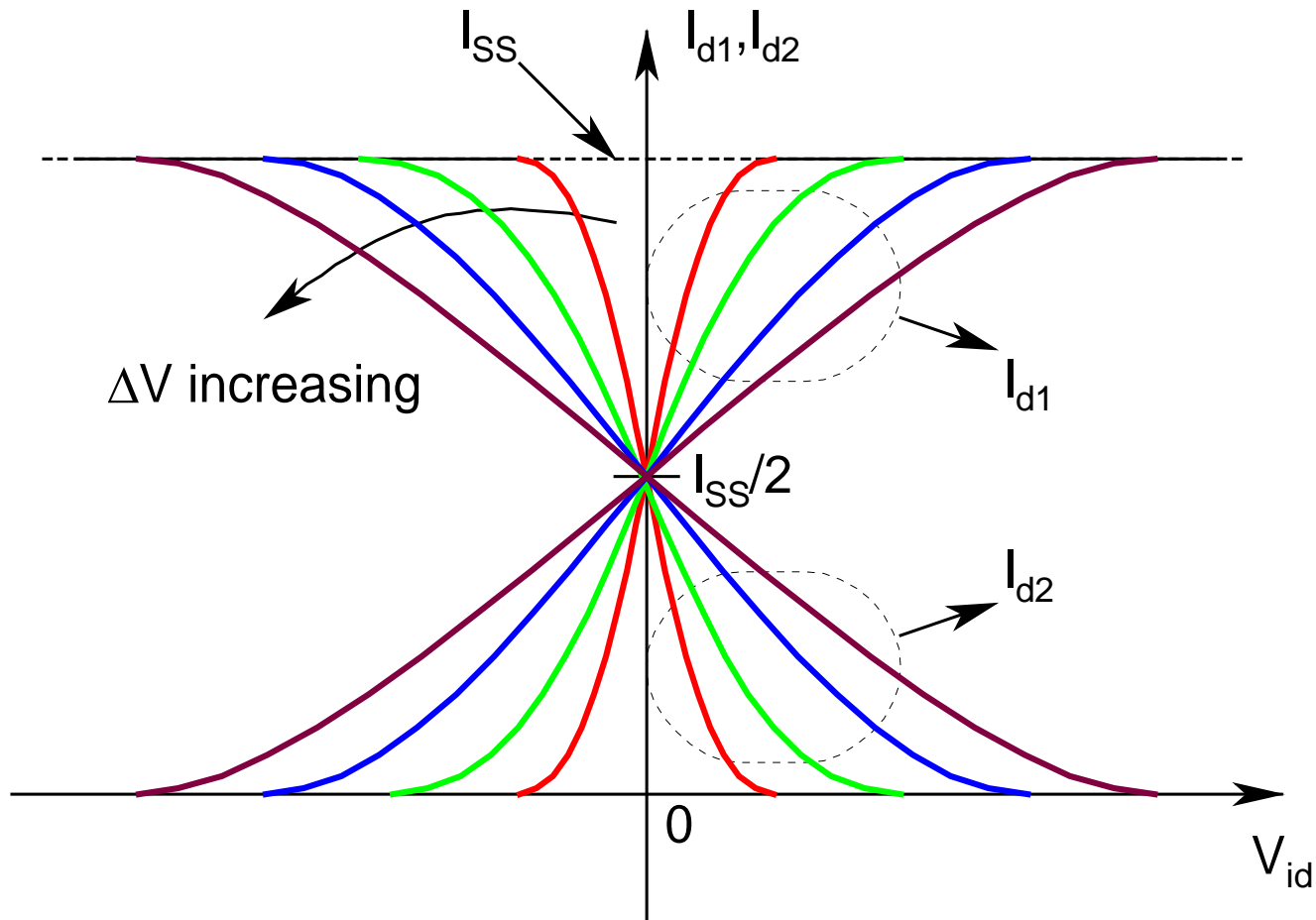
- To find the **Linear Range**, use **Eq.(1)** and put either I_{d1} or I_{d2} equal to I_{SS} :

$$\begin{aligned}\Rightarrow V_{id} &= \pm \sqrt{\frac{2I_{SS}}{k'_N (W/L)}} = \pm \sqrt{2} \left(\sqrt{\frac{2I_{d1}}{k'_N (W/L)}} \right) \Big|_{V_{id}=0} \\ &= \pm \sqrt{2} (\Delta V) \Big|_{V_{id}=0}\end{aligned}$$

since for $V_{id} = 0$, $I_{SS} = 2I_{d1} = 2I_{d2}$

ΔV = Gate Overdrive for M_1/M_2 for $V_{id} = 0$

- Thus, the Linear Range is a function of I_{SS} and $(W/L) \Rightarrow$ Tremendous flexibility!
- Recall: In npn DA, this Linear Range was $\pm 4V_T$, and depended only on temperature



The Current Transfer Characteristics of an NMOS DA